SOT223 P-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ZVP2110G

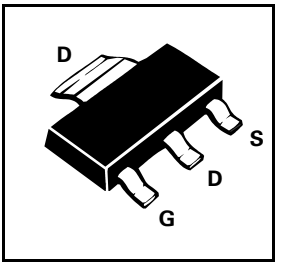
ISSUE 2 – MARCH 94 ✪

FEATURES

* 100 Volt V_{DS}
* $R_{DS(on)}$=8Ω

COMPLEMENTARY TYPE – ZVN2110G

PARTMARKING DETAIL – ZVP2110



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	-100	V
Continuous Drain Current at T_{amb}=25°C	I_D	-310	mA
Pulsed Drain Current	I_{DM}	-3	A
Gate Source Voltage	V_{GS}	± 20	V
Power Dissipation at T_{amb}=25°C	P_{tot}	2	W
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	°C

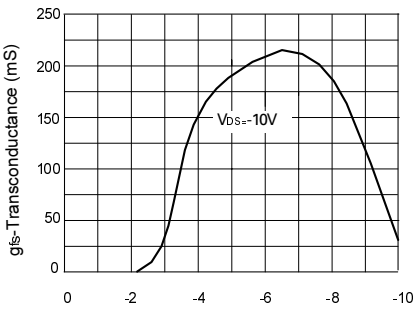
ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	-100		V	I_D=-1mA, V_{GS}=0V
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.5	-3.5	V	ID=-1mA, V_{DS}= V_{GS}
Gate-Body Leakage	I_{GSS}		20	nA	V_{GS}=± 20V, V_{DS}=0V
Zero Gate Voltage Drain Current	I_{DSS}		-1 -100	μA μA	V_{DS}=-100 V, V_{GS}=0 V_{DS}=-80 V, V_{GS}=0V, T=125°C(2)
On-State Drain Current(1)	$I_{D(on)}$	-750		mA	V_{DS}=-25 V, V_{GS}=-10V
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		8	Ω	V_{GS}=-10V,I_D=-375mA
Forward Transconductance (1)(2)	g_{fs}	125		mS	V_{DS}=-25V,I_D=-375mA
Input Capacitance (2)	C_{iss}		100	pF	V_{DS}=-25V, V_{GS}=0V, f=1MHz
Common Source Output Capacitance (2)	C_{oss}		35	pF	
Reverse Transfer Capacitance (2)	C_{rss}		10	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$		7	ns	V_{DD}≈-25V, I_D=-375mA
Rise Time (2)(3)	t_r		15	ns	
Turn-Off Delay Time (2)(3)	$t_{d(off)}$		12	ns	
Fall Time (2)(3)	t_f		15	ns	

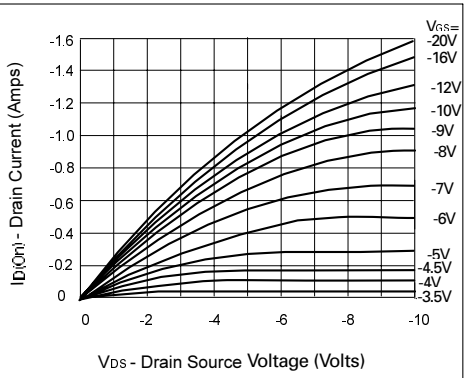
(1) Measured under pulsed conditions. Width=300μs. Duty cycle ≤2% (2) Sample test.

ZVP2110G

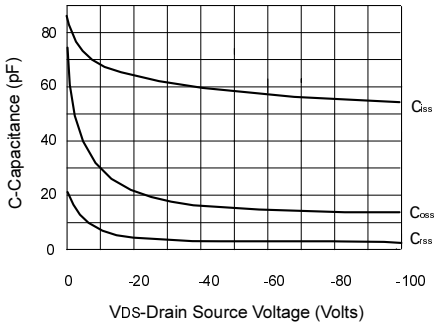
TYPICAL CHARACTERISTICS



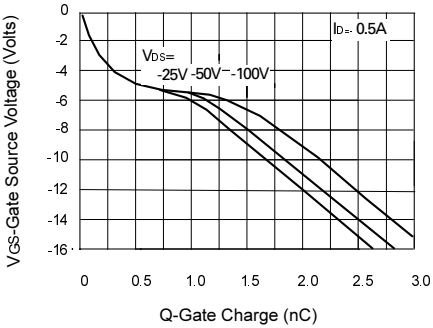
Transconductance v gate-source voltage



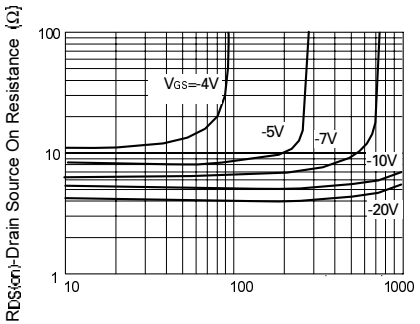
Saturation Characteristics



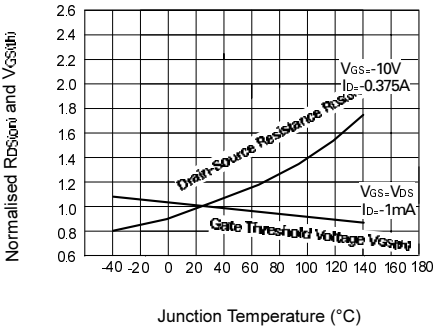
Capacitance v drain-source voltage



Gate charge v gate-source voltage



On-resistance v drain current



Normalised $R_{DS(on)}$ and $V_{GS(th)}$ vs Temperature